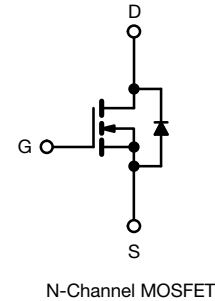
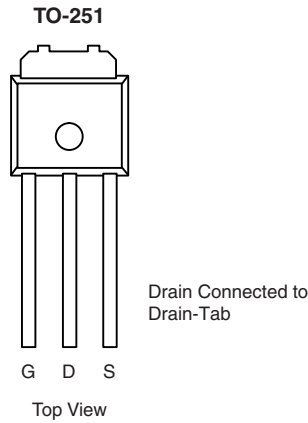


N-Channel 250 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	250	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	0.176
Q_g max. (nC)	68	
Q_{gs} (nC)	11	
Q_{gd} (nC)	35	
Configuration	Single	

FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- Fast switching
- Ease of paralleling
- Simple drive requirements



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V _{DS}	250	V
Gate-Source Voltage			V _{GS}	± 20	
Continuous Drain Current	V _{GS} at 10 V	T _C = 25 °C	I _D	17	A
		T _C = 100 °C		11	
Pulsed Drain Current ^a			I _{DM}	56	
Linear Derating Factor				1.0	W/°C
Single Pulse Avalanche Energy ^b			E _{AS}	550	mJ
Repetitive Avalanche Current ^a			I _{AR}	17	A
Repetitive Avalanche Energy ^a			E _{AR}	13	mJ
Maximum Power Dissipation	T _C = 25 °C		P _D	125	W
Peak Diode Recovery dV/dt ^c			dV/dt	4.8	V/ns
Operating Junction and Storage Temperature Range			T _J , T _{stg}	-55 to +150	°C
Soldering Recommendations (Peak temperature) ^d		for 10 s		300	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

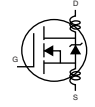
Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$, starting $T_J = 25\text{ }^{\circ}\text{C}$, $L = 4.5\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 14\text{ A}$ (see fig. 12).
- $I_{SD} \leq 14\text{ A}$, $dI/dt \leq 150\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^{\circ}\text{C}$.
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS

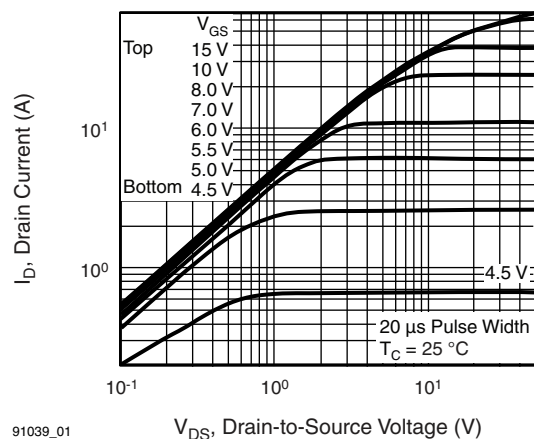
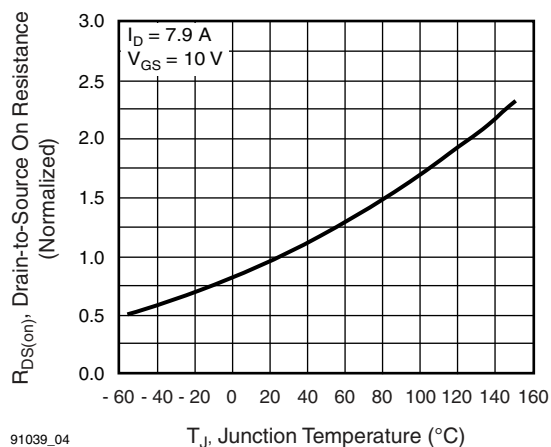
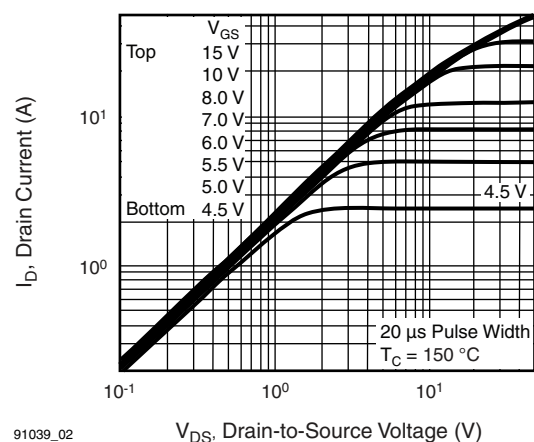
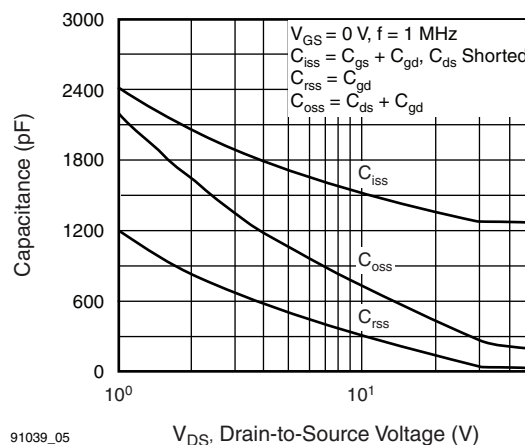
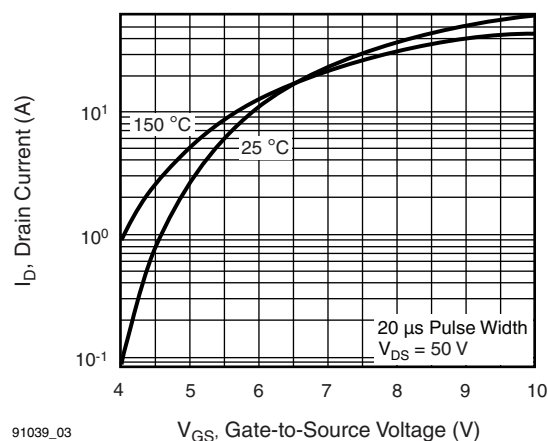
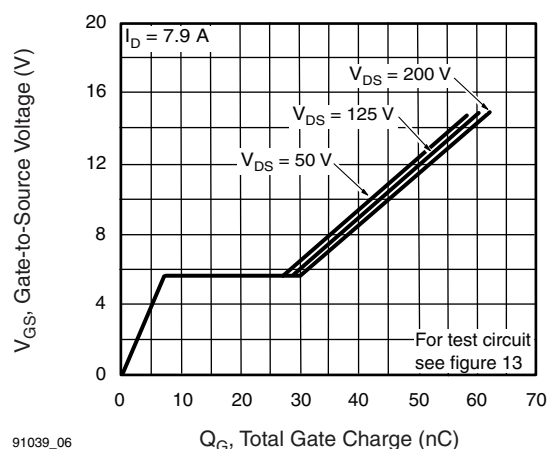
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.0	

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	250	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^{\circ}\text{C}$, $I_D = 1\text{ mA}$	-	0.34	-	V/ $^{\circ}\text{C}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 250\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	25	μA
		$V_{DS} = 200\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 8.4\text{ A}^b$	-	0.176	-	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 8.4\text{ A}^b$	6.7	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 5	-	1300	-	pF
Output Capacitance	C_{oss}		-	330	-	
Reverse Transfer Capacitance	C_{rss}		-	85	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$, $I_D = 7.9\text{ A}$, $V_{DS} = 200\text{ V}$, see fig. 6 and 13 ^b	-	-	68	nC
Gate-Source Charge	Q_{gs}		-	-	11	
Gate-Drain Charge	Q_{gd}		-	-	35	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 125\text{ V}$, $I_D = 7.9\text{ A}$, $R_g = 9.1\text{ }\Omega$, $R_D = 8.7\text{ }\Omega$, see fig. 10 ^b	-	11	-	ns
Rise Time	t_r		-	24	-	
Turn-Off Delay Time	$t_{d(off)}$		-	53	-	
Fall Time	t_f		-	49	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Gate Input Resistance	R_g	$f = 1\text{ MHz}$, open drain	0.3	-	1.2	Ω
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	14	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	56	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_S = 14\text{ A}$, $V_{GS} = 0\text{ V}^b$	-	-	1.8	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_F = 7.9\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	250	500	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	2.3	4.6	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
 b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics, $T_C = 25^\circ\text{C}$

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics, $T_C = 150^\circ\text{C}$

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

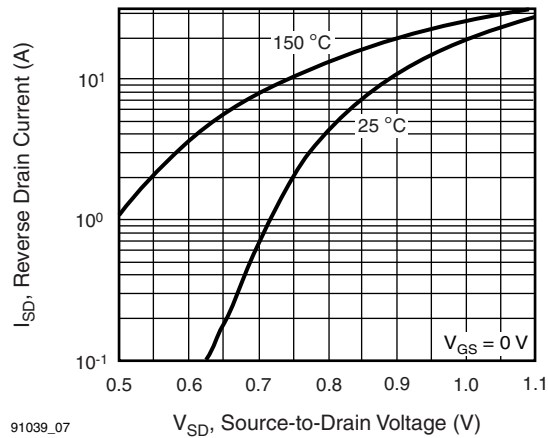


Fig. 7 - Typical Source-Drain Diode Forward Voltage

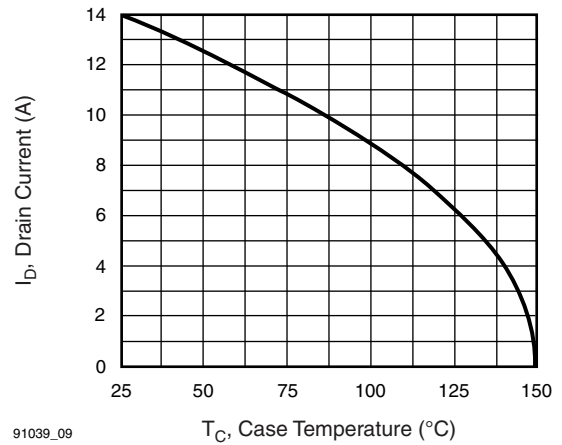


Fig. 9 - Maximum Drain Current vs. Case Temperature

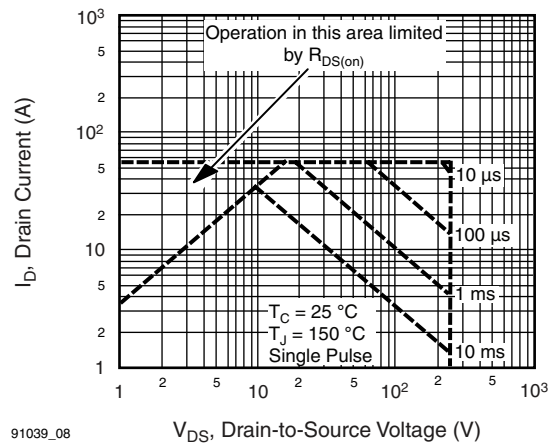


Fig. 8 - Maximum Safe Operating Area

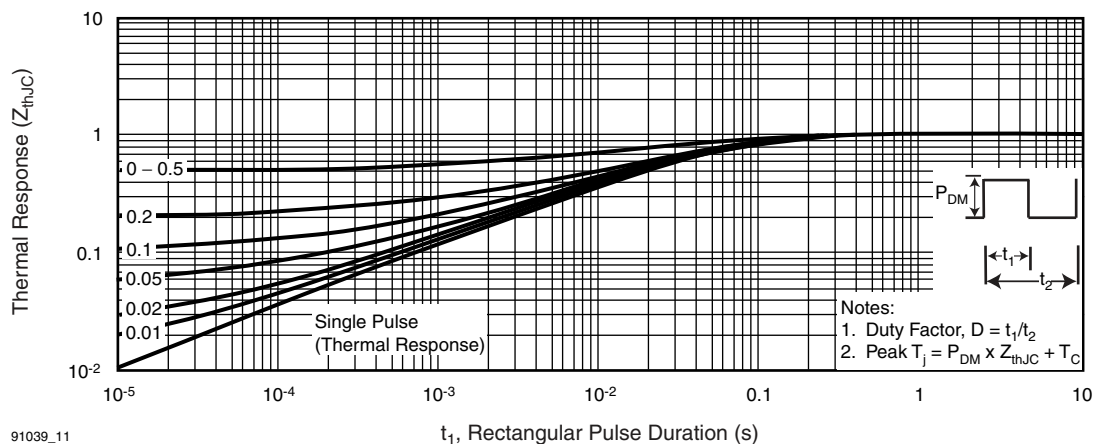
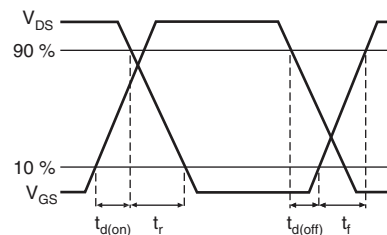
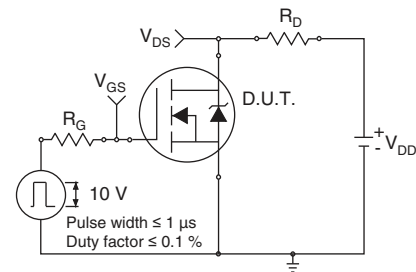


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

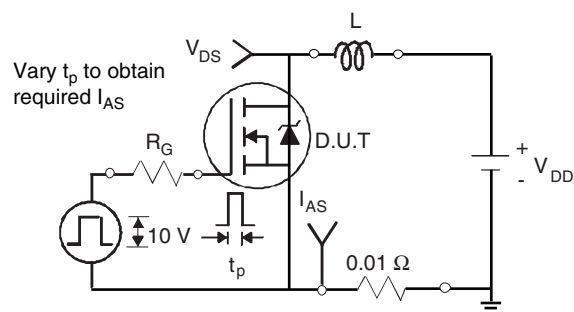


Fig. 12a - Unclamped Inductive Test Circuit

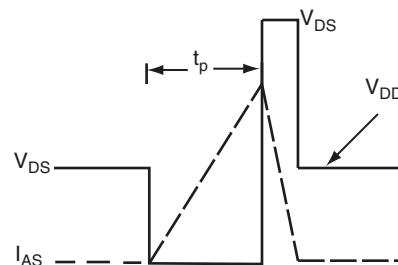


Fig. 12b - Unclamped Inductive Waveforms

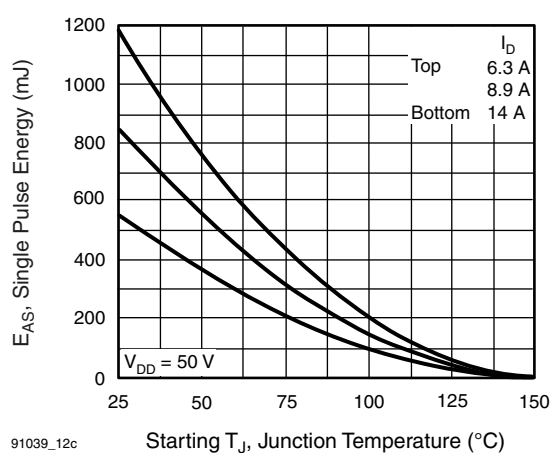


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

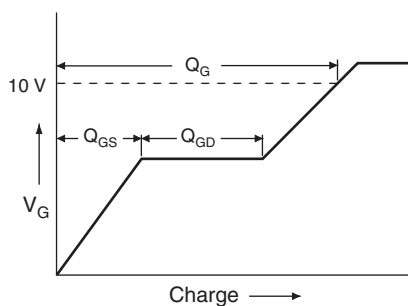


Fig. 13a - Basic Gate Charge Waveform

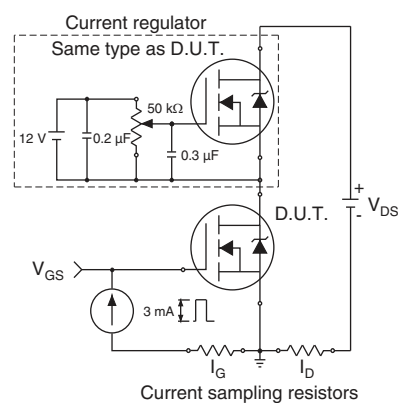
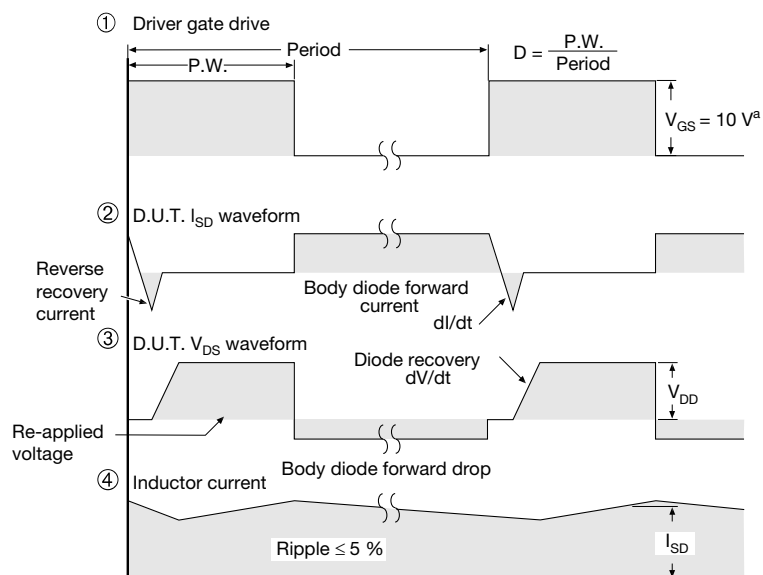
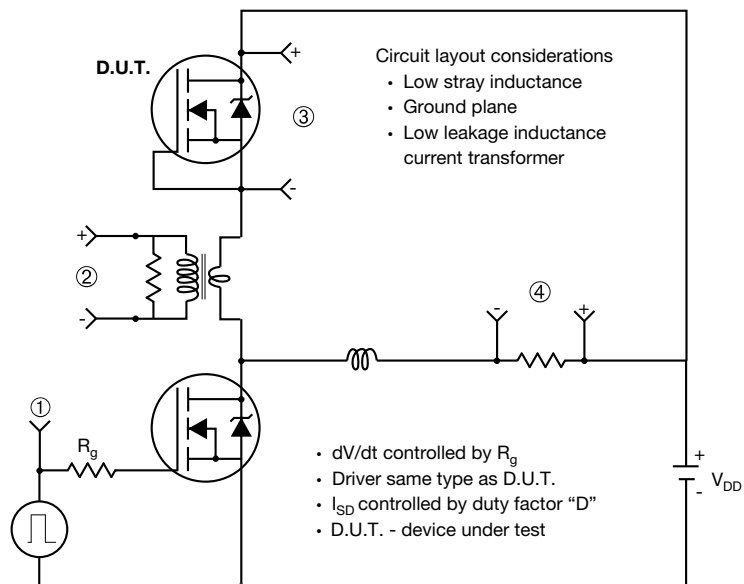


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit

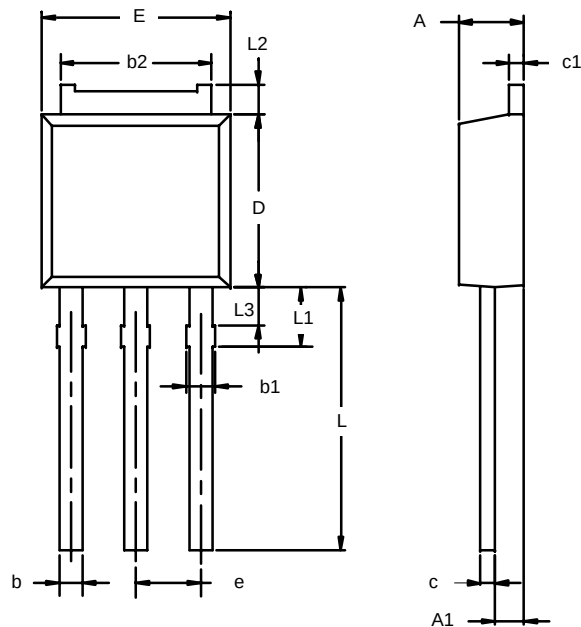


Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

TO-251AA (DPAK)



Note: Dimension L3 is for reference only.

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	2.21	2.38	0.087	0.094
A1	0.89	1.14	0.035	0.045
b	0.71	0.89	0.028	0.035
b1	0.76	1.14	0.030	0.045
b2	5.23	5.43	0.206	0.214
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
E	6.48	6.73	0.255	0.265
e	2.28 BSC		0.090 BSC	
L	3.89	9.53	0.153	0.375
L1	1.91	2.28	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.15	1.52	0.045	0.060

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